BC635, BC637, BC639, BC639-16

High Current Transistors NPN Silicon

Features

• Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC635 BC637 BC639	V _{CEO}	45 60 80	Vdc
Collector-Base Voltage BC635 BC637 BC639	V _{CBO}	45 60 80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	۱ _C	1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	800 12	mW mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

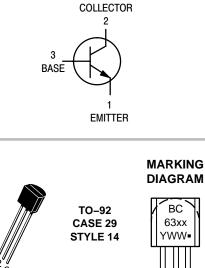
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W



ON Semiconductor[®]

http://onsemi.com





ORDERING INFORMATION

Device	Package	Shipping [†]			
BC635RL1	TO-92	2000/Tape & Reel			
BC635ZL1	TO-92	2000/Ammo Pack			
BC637	TO-92	5000 Units/Box			
BC639	TO-92	5000 Units/Box			
BC639RL1	TO-92	2000/Tape & Reel			
BC639ZL1	TO-92	2000/Ammo Pack			
BC639-16ZL1	TO-92	2000/Ammo Pack			
BC639–16ZL1G	TO-92 (Pb-Free)	2000/Ammo Pack			

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

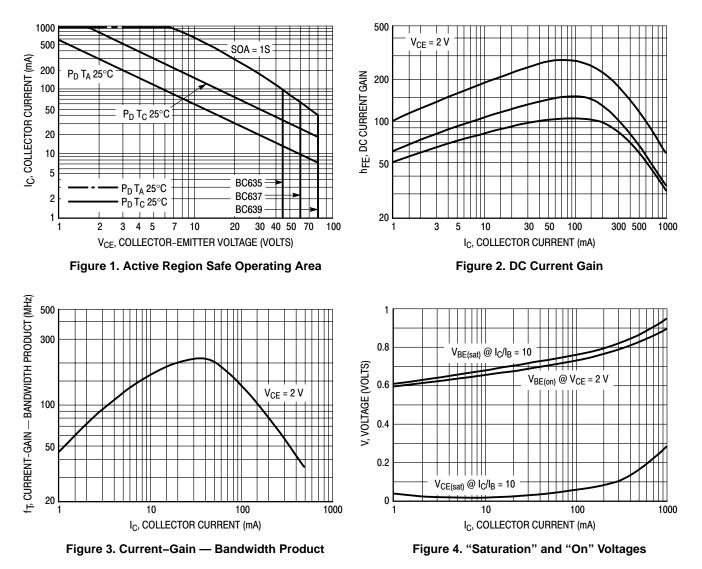
BC635, BC637, BC639, BC639-16

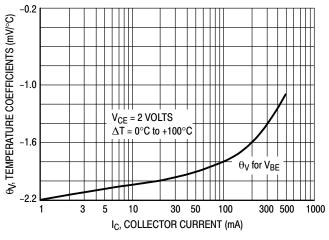
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	
Collector – Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 μ Adc, I _B = 0)	BC635 BC637 BC639	V _{(BR)CEO}	45 60 80	- - -	- - -	Vdc
Collector – Emitter Zero–Gate Breakdown Voltar ($I_C = 100 \ \mu Adc, I_B = 0$)	ge ⁽¹⁾ BC639–16	V _{(BR)CES}	120	_	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	BC635 BC637 BC639	V _{(BR)CBO}	45 60 80	- - -	- - -	Vdc
Emitter – Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$		V _{(BR)EBO}	5.0	-	-	Vdc
		I _{CBO}			100 10	nAdc μAdc
ON CHARACTERISTICS (Note 1)						
DC Current Gain (I _C = 5.0 mAdc, V _{CE} = 2.0 Vdc) (I _C = 150 mAdc, V _{CE} = 2.0 Vdc) (I _C = 500 mA, V _{CE} = 2.0 V)	BC635 BC637 BC639 BC639–16ZLT1	hFE	25 40 40 100 25	- - - - -	_ 250 160 160 250 _	-
Collector – Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc)		V _{CE(sat)}	-	-	0.5	Vdc
Base – Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)		V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS		-	-	-	-	
Current – Gain – Bandwidth Product ($I_C = 50 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}, f = 100 \text{ MHz}$)		f _T	-	200	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C _{ob}	-	7.0	-	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ib}	-	50	-	pF

1. Pulse Test: Pulse Width $\leq 300~\mu s,$ Duty Cycle 2.0%.

BC635, BC637, BC639, BC639-16

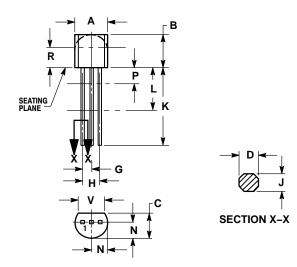






PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. Controlling dimension: Inch. Contour of Package Beyond Dimension R Is uncontrolled.
- 3.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
Κ	0.500		12.70		
L	0.250		6.35		
Ν	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

PIN 1. EMITTER COLLECTOR 2. 3. BASE

ON Semiconductor and in the registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other applications Intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.